

FDN338P

P-Channel 2.5V Specified PowerTrench[®] MOSFET

General Description

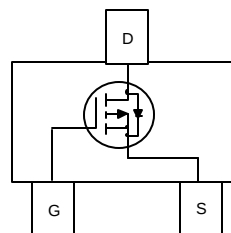
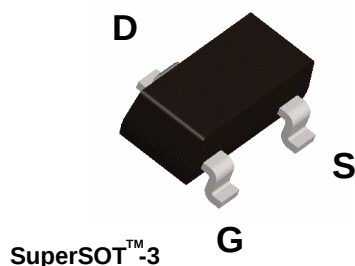
This P-Channel 2.5V specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. It has been optimized for battery power management applications.

Applications

- Battery management
- Load switch
- Battery protection

Features

- -1.6 A, -20 V. $R_{DS(ON)} = 115\text{ m}\Omega$ @ $V_{GS} = -4.5\text{ V}$
 $R_{DS(ON)} = 155\text{ m}\Omega$ @ $V_{GS} = -2.5\text{ V}$
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- SuperSOT[™]-3 provides low $R_{DS(ON)}$ and 30% higher power handling capability than SOT23 in the same footprint



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	-20	V
V _{GSS}	Gate-Source Voltage	±8	V
I _D	Drain Current – Continuous	-1.6	A
	– Pulsed	-5	
P _D	Maximum Power Dissipation (Note 1a) (Note 1b)	0.5 0.46	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.338	FDN338P	7"	8mm	3000 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	–20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C		–16		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}$, $V_{GS} = 0\text{ V}$			–1	μA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 8\text{ V}$, $V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -8\text{ V}$, $V_{DS} = 0\text{ V}$			–100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	–0.4	–0.8	–1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C		2.7		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5\text{ V}$, $I_D = -1.6\text{ A}$ $V_{GS} = -2.5\text{ V}$, $I_D = -1.3\text{ A}$ $V_{GS} = -4.5\text{ V}$, $I_D = -1.6\text{ A}$, $T_J = 125^\circ\text{C}$		88 117 116	115 155 165	m Ω
$I_{D(on)}$	On–State Drain Current	$V_{GS} = -4.5\text{ V}$, $V_{DS} = -5\text{ V}$	–5			A
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{ V}$, $I_D = -1.6\text{ A}$		6		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$		451		pF
C_{oss}	Output Capacitance			75		pF
C_{rss}	Reverse Transfer Capacitance			33		pF

Switching Characteristics (Note 2)

$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -10\text{ V}$, $I_D = -1\text{ A}$, $V_{GS} = -4.5\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		10	20	ns
t_r	Turn–On Rise Time			11	20	ns
$t_{d(off)}$	Turn–Off Delay Time			16	29	ns
t_f	Turn–Off Fall Time			6.5	13	ns
Q_g	Total Gate Charge	$V_{DS} = -10\text{ V}$, $I_D = -1.6\text{ A}$, $V_{GS} = -4.5\text{ V}$		4.4	6.2	nC
Q_{gs}	Gate–Source Charge			1.1		nC
Q_{gd}	Gate–Drain Charge			0.7		nC

Drain–Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain–Source Diode Forward Current				–0.42	A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = -0.42$ (Note 2)		–0.7	–1.2	V

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in^2 pad of 2 oz. copper.



b) 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

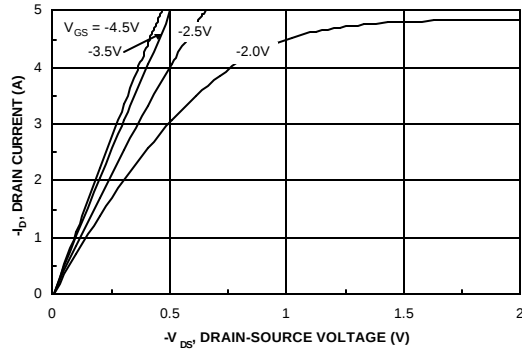


Figure 1. On-Region Characteristics.

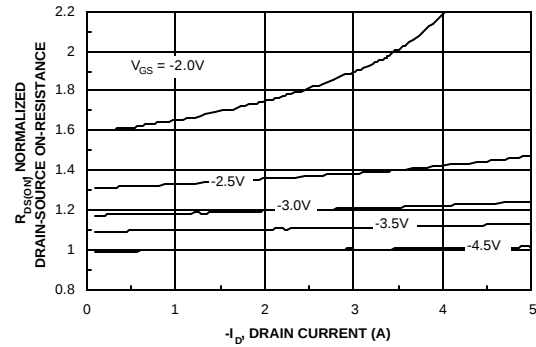


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

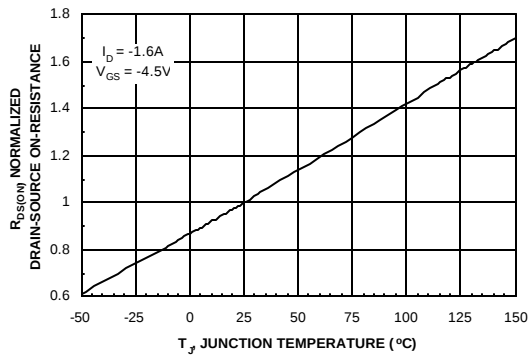


Figure 3. On-Resistance Variation with Temperature.

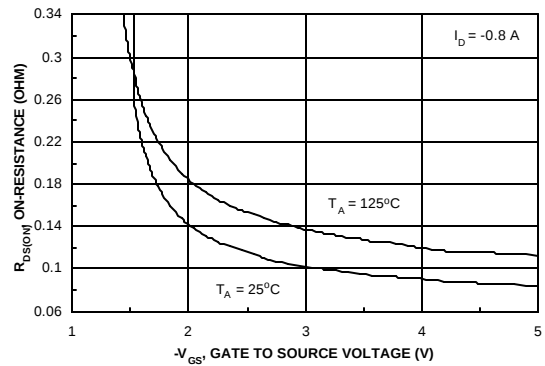


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

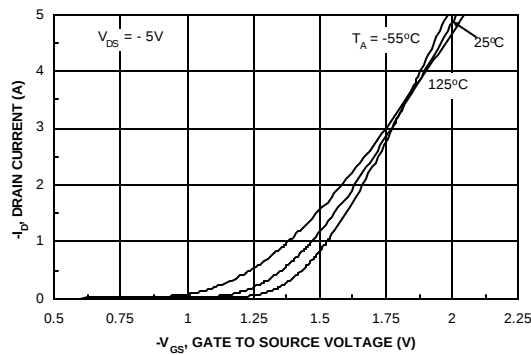


Figure 5. Transfer Characteristics.

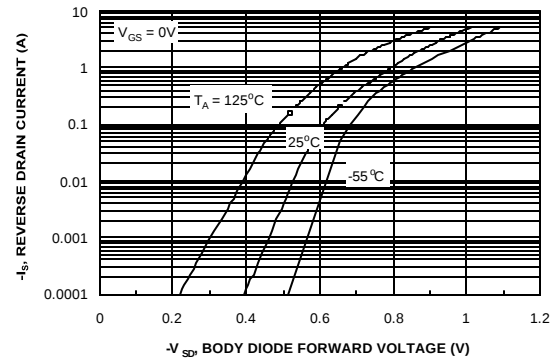


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

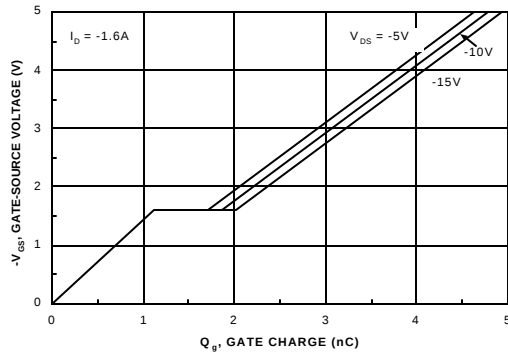


Figure 7. Gate Charge Characteristics.

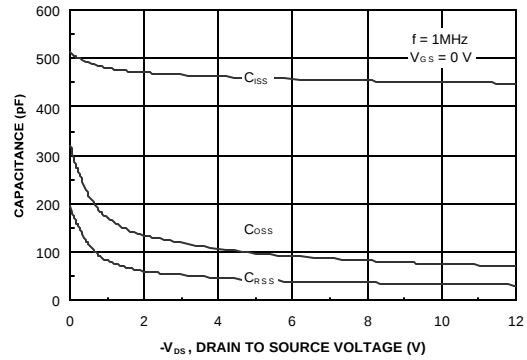


Figure 8. Capacitance Characteristics.

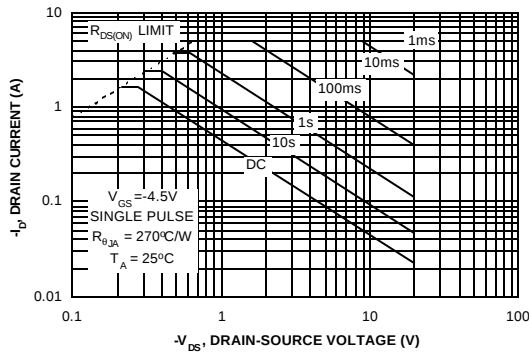


Figure 9. Maximum Safe Operating Area.

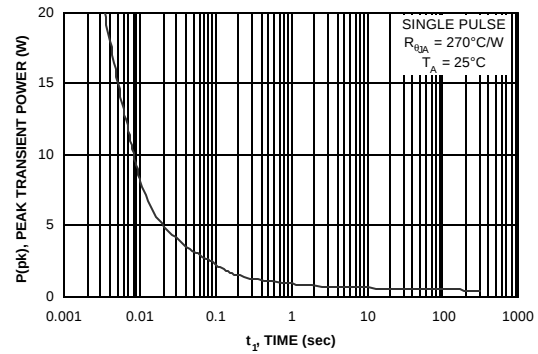


Figure 10. Single Pulse Maximum Power Dissipation.

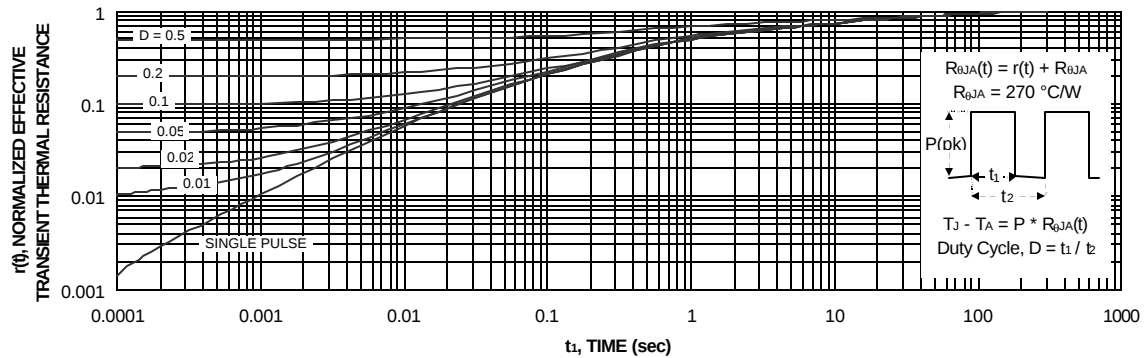


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

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DOME™	HiSeC™	PowerTrench [®]	SuperSOT™-8	
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EnSigna™	MicroFET™	QT Optoelectronics™	TruTranslation™	
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